

# OT408 1 A Four-quadrant triac, high surge capability Rev. 01 — 30 July 2008

**Product data sheet** 

### 1. Product profile

### 1.1 General description

Passivated sensitive gate triac in a SOT223 surface-mountable plastic package

### 1.2 Features

- Sensitive gate
- Direct interfacing to logic level ICs
- High surge capability

### 1.3 Applications

- Home appliances
- Small lamp control

### 1.4 Quick reference data

- V<sub>DRM</sub> ≤ 800 V
- I<sub>TSM</sub> ≤ 12.5 A (t = 20 ms)
- I<sub>T(RMS)</sub>  $\leq$  1 A

- Gate triggering in four quadrants
- Direct interfacing to low power gate drive circuits
- High blocking voltage of 800 V
- Low power motor control
- Low power loads in industrial process control
- I<sub>GT</sub> ≤ 5 mA
- I<sub>GT</sub>  $\leq$  7 mA (T2– G+)

### 2. Pinning information

Table 1.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	main terminal 1 (T1)		NI
2	main terminal 2 (T2)		T2-T1
3	gate (G)		`G sym051
4	mounting base; main terminal 2 (T2)		
		SOT223	



## 3. Ordering information

Table 2. Ordering information						
Type number	Package					
	Name	Description	Version			
OT408	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			

## 4. Limiting values

#### Table 3. Limiting values

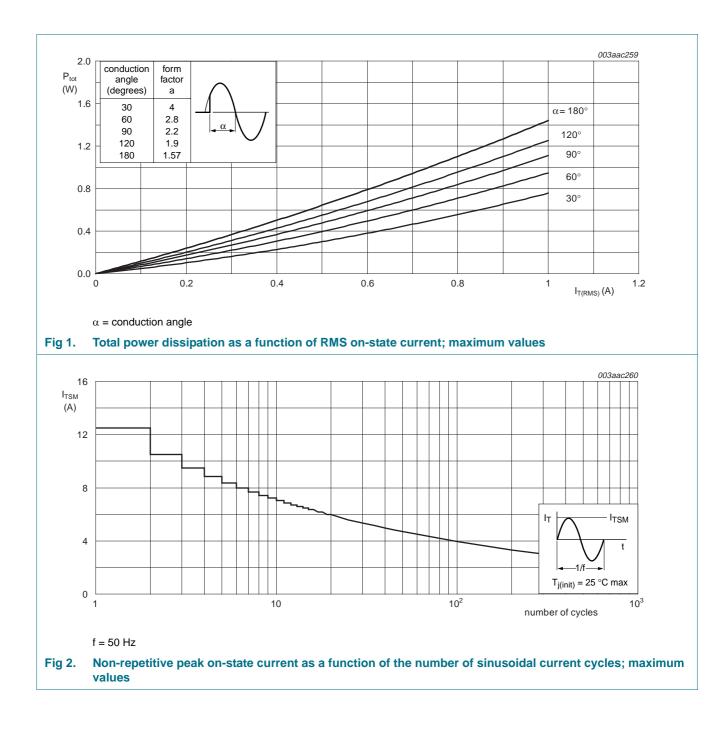
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DRM</sub>	repetitive peak off-state voltage		-	800	V
V <sub>RRM</sub>	repetitive peak reverse voltage		-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{sp} \le 103 \text{ °C}$ ; see Figure 4 and 5	-	1	А
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_j = 25 \text{ °C}$ prior to surge; see Figure 2 and 3			
		t = 20 ms	-	12.5	А
		t = 16.7 ms	-	13.8	А
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms	-	0.78	A <sup>2</sup> s
dI <sub>T</sub> /dt	rate of rise of on-state current	$\begin{split} I_{TM} = 1 \text{ A}; \ I_G = 20 \text{ mA}; \\ dI_G/dt = 0.2 \text{ A}/\mu\text{s} \end{split}$			
		T2+ G+	-	50	A/μs
		T2+ G-	-	50	A/µs
		T2-G-	-	50	A/μs
		T2– G+	-	10	A/μs
I <sub>GM</sub>	peak gate current		-	1	А
P <sub>GM</sub>	peak gate power		-	2	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.1	W
T <sub>stg</sub>	storage temperature		-40	+150	°C
Tj	junction temperature		-	125	°C

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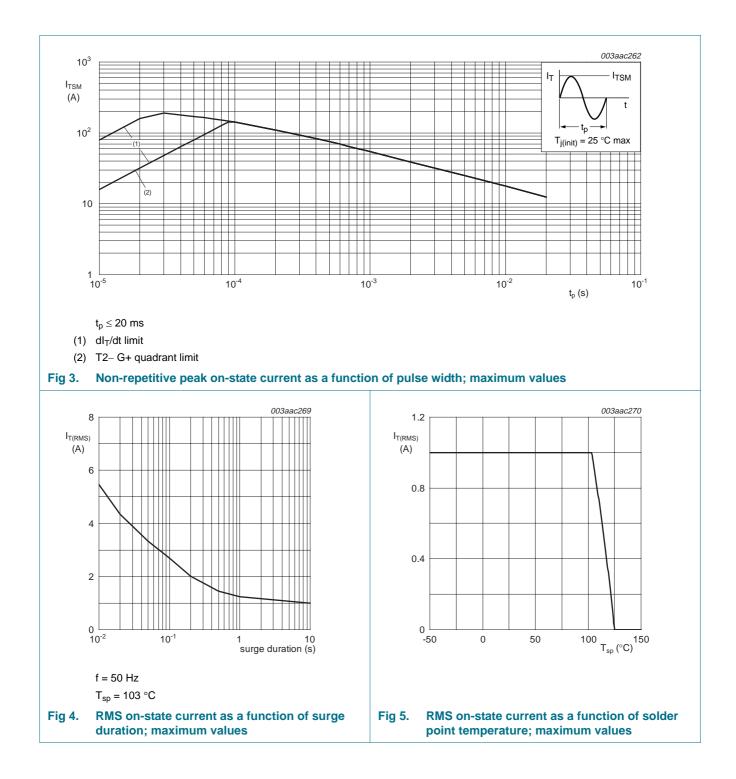


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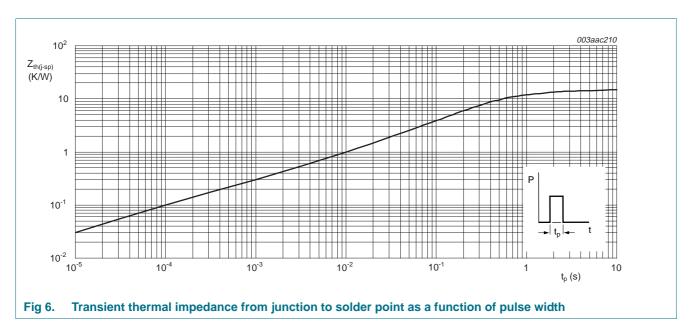


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### 5. Thermal characteristics

Table 4.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point	full cycle; see <u>Figure 6</u>	-	-	15	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to	full cycle				
	ambient	for minimum footprint see <u>Figure 13</u>	-	- 156 -	-	K/W
		for pad area see Figure 14	- 70	70	-	K/W



### 6. Static characteristics

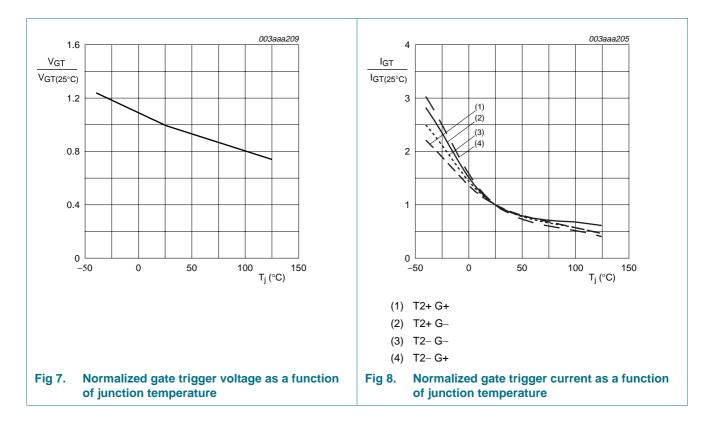
#### Table 5. Static characteristics

 $T_j = 25 \circ C$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ see } \frac{\text{Figure 8}}{1000 \text{ Figure 8}}$				
		T2+ G+	-	-	5	mA
		T2+ G–	-	-	5	mA
		T2- G-	-	-	5	mA
		T2– G+	-	-	7	mA
IL	latching current	$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ see } \frac{\text{Figure 10}}{10}$				
		T2+ G+	-	-	10	mA
		T2+ G–	-	-	20	mA
		T2- G-	-	-	10	mA
		T2– G+	-	-	10	mA
I <sub>H</sub>	holding current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ see } \frac{\text{Figure } 11}{100000000000000000000000000000000$	-	-	10	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1 A; see <u>Figure 9</u>	-	1.3	1.6	V
V <sub>GT</sub>	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ see } \frac{\text{Figure 7}}{100000000000000000000000000000000000$	-	-	1.3	V
		$V_D = V_{DRM}; I_T = 0.1 \text{ A}; T_j = 125 ^{\circ}\text{C}$	0.2	-	-	V
I <sub>D</sub>	off-state current	$V_D = V_{DRM(max)}; T_j = 125 \ ^{\circ}C$	-	-	0.5	mA

## 7. Dynamic characteristics

Table 6.	Dynamic characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM} = 0.67 V_{DRM(max)}$ ; $T_j = 110 \text{ °C}$ ; exponential waveform; gate open circuit	20	-	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_{DM}$ = 400 V; T <sub>j</sub> = 110 °C; I <sub>TM</sub> = 1 A; dI <sub>com</sub> /dt = 0.44 A/ms	1	-	-	V/µs

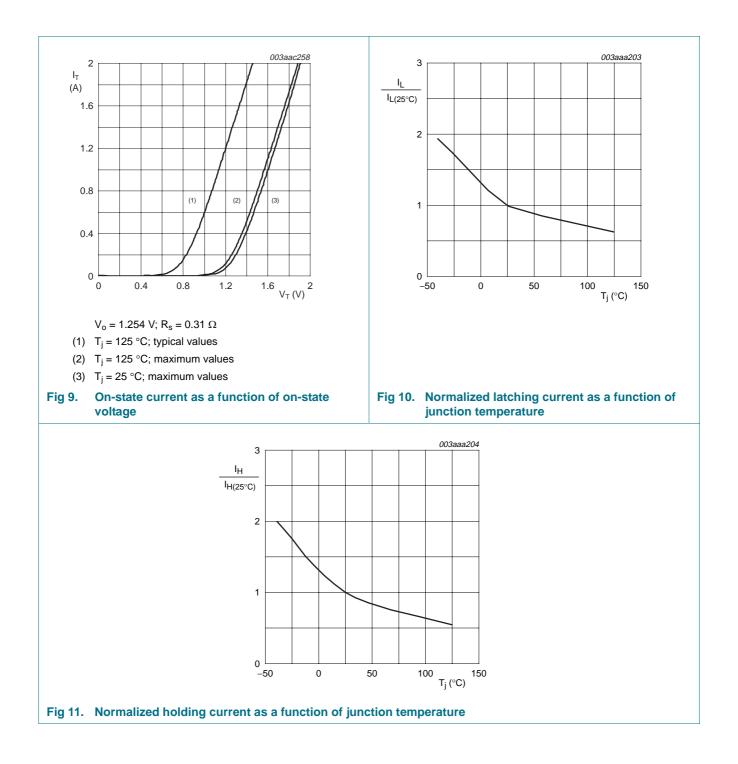


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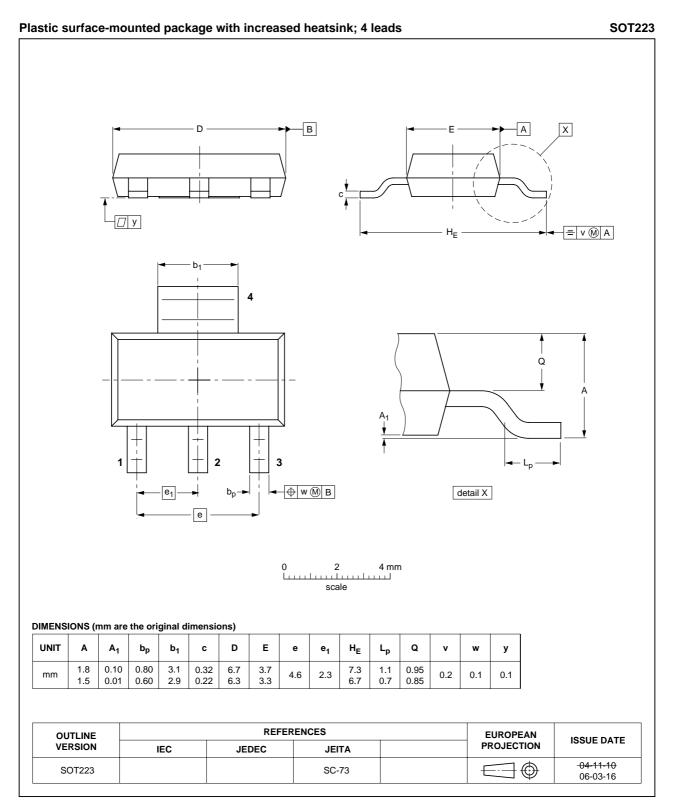
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### 8. Package outline

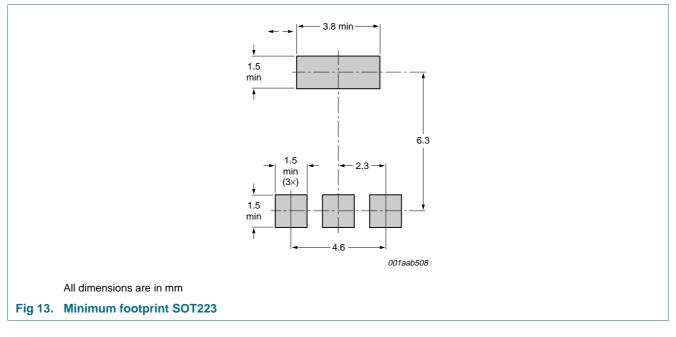


#### Fig 12. Package outline SOT223 (SC-73)

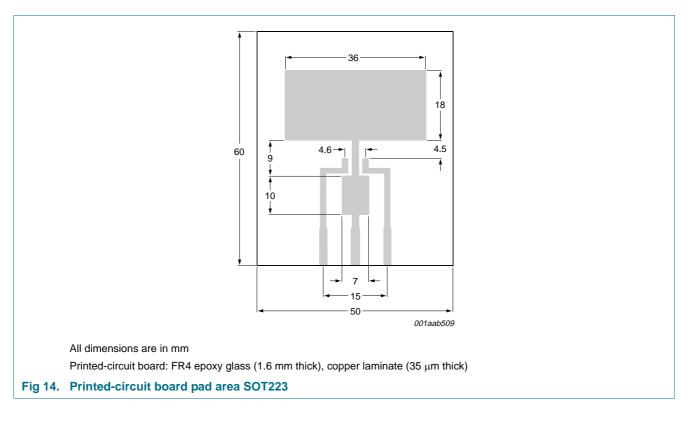
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### 9. Mounting

### 9.1 Mounting instructions



### 9.2 Printed-circuit board



## **10. Revision history**

Table 7. Revision hist	Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
OT408_1	20080730	Product data sheet	-	-	

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Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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